

**IN THE SPECIFICATION:**

Please revise Page 34, Lines 11-26 to read as follows:

With reference to FIGS. 9B and 8B, the p-electrode 66 includes ridged projections 66A substantially equally spaced in a parallel relation (substantially uniformly distributed), thereby  
5 defining a striped projection-depression surface profile 66B. Each projection 66A makes a contact at the top thereof with the undersurface of the p-AlGa<sub>N</sub> layer 60. Grooved depressions 66C in the projection-depression surface profile 66B are filled with an insulator 92 made of a silicon oxide. Alternatively to the silicon oxide, the insulator 92 may be made of any of the materials mentioned in the embodiment 1, including Ta<sub>2</sub>O<sub>5</sub>. The semiconductor  
10 multilayer structure 56 has linear lattice defects oriented in the laminating direction. These linear lattice defects, also known as dislocations, are areas in a crystal where the atomic arrangement is broken. Through the manufacturing process, the lattice defects are controlled to appear in regions where the insulator 92 will be disposed. Details of the lattice defects are given later in a description of a manufacturing method of the LED chip 52.